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Additional Information

Effect of Guanidinium on the Optical Properties and Structure of the Methylammonium Lead Halide Perovskite

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Abstract

The stability and performance of perovskite-based solar cells can be improved changing the nature of the organic cation. Herein, mixed methylammonium–guanidinium perovskites ($\text{MA}_{1-x}\text{GA}_x\text{PbI}_3$) are structurally and optically characterized. The Pawley fit method indicates the formation of the iodide halide GAPbI_3 tetragonal phase (P42₁-NMC). Up to 20% of the guanidinium cation was incorporated in the methylammonium lead iodide perovskite, producing a lattice enlargement, which was investigated studying the shift of the diffraction peaks of the MAPbI_3 (I4₁-CM) tetragonal lattice. Long-term stability was tested, resulting in improved mixed perovskites with a low GA content. The bandgap shifted to lower energies. The absorption bandgap diminished slightly when the GA cation substituted up to 20 % of MA in MAPbI_3 , degrading when the GA amount in the mixed perovskite is larger. FESEM morphological analysis was performed showing that a uniform thin film was deposited. PL studies showed that only shallow defects had been introduced.

Keywords: Thin film perovskite, Mixed halide perovskite, Gap energy, Chemical composition, Photoluminescence.

1. Introduction

The methylammonium lead halide perovskite ($\text{CH}_3\text{NH}_3\text{PbX}_3$, X= halogen; $\text{CH}_3\text{NH}_3 = \text{MA}$) and its mixed-halide crystals have been studied in depth in recent years, showing many optimal optoelectronic features of an ideal solar cell absorber. Among these properties, a favorable bandgap, high absorption coefficient, excellent charge mobility, high photoluminescence quantum efficiencies, small exciton binding energy, tunable bandgap and a reasonably defect tolerance [1-6] can be highlighted. These features have given perovskites an important role as an absorber in photovoltaic cells [7-11]. Indeed, in a relatively short period of time, devices based on perovskite materials have achieved a performance of certified 22.1% PCE [12], starting from a conversion efficiency of only 3.9% in 2009 [1] and being, at the same time, more cost-effective than the silicon solar ones.

When it comes to the synthesis of the perovskite, a wide variety of procedures has been employed such as vacuum deposition [13], vapor-assisted solution processing [14], atomic layer deposition [15], solution processing in one or two steps [16,17] etc. However, MAPbI_3 perovskite materials are still not stable enough in the long term to become fully affordable and scalable. MAPbI_3 perovskite materials have been proven to degrade under humid conditions [18], and several techniques have been applied in order to improve stability [19-21]. In this context, it has been found that MAPbBr_3 is less sensitive to humidity [22,23], but at the expense of losing absorption properties. Some researchers focused on mixed halide perovskites $\text{MAPbI}_{3-x}\text{Br}_x$ and $\text{MAPbI}_{3-x}\text{Cl}_x$ as the substitution of iodine by chloride or bromide atoms leads to a significant improvement of perovskite stability [24,25].

Defect energy levels have been shown to be situated relatively shallow [26,27] and although it had been hypothesized that grain boundaries do not contribute significantly to recombination losses in perovskites, it has been proved that they are much more harmful than previously assumed [28,29]. This means that if it were possible to mitigate nonradiative carrier losses, the efficiency of perovskite solar cells could be substantially improved. In order to successfully mitigate such charge carrier losses, recombination pathways within the perovskite and device have been suppressed. Employing additives in perovskite methylammonium lead iodide seems to

be an efficient method to tune its properties such as defect density and charge carrier lifetime.

Regarding this topic, under-coordinated ions that may exist at grain boundaries and surfaces that can act as charge carrier trap/recombination centers [30,31] have been described.

Different passivation methods have been employed up to now. For example, an iodopentafluorobenzene (IPFB) post-treatment has been used to passivate under-coordinated iodine [30], thiophene and pyridine have been employed to passivate under-coordinated Pb ions [31] and, recently, Br and Cl have been suggested to assist in suppressing recombination and decoupling electron–hole pairs [32,33].

In order to improve performance, the guanidinium organic molecule CH_6N_3^+ (GA) has been investigated as an additive for dye-sensitized solar cells (DSSCs), in which it serves to passivate TiO_2 surfaces. Also, it has been studied as an additive in MAPbI_3 in order to improve structure, stability and performance. GA has a larger size (278 pm) than MA (217 pm), which can lead to different perovskite structures and/or behaviors [36,37], therefore it is necessary to investigate the consequences of the GA addition in detail. Some authors suggest that bias-induced motion and hysteric effects might be influenced by the zero-dipole moment of GA [34,35].

Very recently, a passivation effect through partial GA incorporation in perovskite films has been demonstrated [34], obtaining a significant mitigation of nonradiative decay and an enhanced carrier lifetime, high open circuit voltages and improved device performances.

This study presents the structural and optical effects of partial GA incorporation in MAPbI_3 perovskite thin films with the aim of increasing and improving the stability of solar cells.

2. Experimental procedure

2.1 Perovskite fabrication

Guanidinium iodine ($\text{CH}_6\text{N}_3\text{I}$, GAI) was purchased from Sigma Aldrich. Crystalline methylammonium iodide ($\text{CH}_3\text{NH}_3\text{I}$, MAI) powder was synthesized by reacting 0.3 mol of concentrated hydriodic acid (Sigma Aldrich) with 0.3 mol of methylamine (CH_3NH_2)

solution (33% in methanol, Sigma Aldrich) whilst being stirred for 2 h in a 250 mL round-bottom flask kept in an ice bath (0°C). The solvent was evaporated at 50 °C in the rotary evaporator. Then, the precipitate was filtered and recrystallized by solving it in absolute ethanol and precipitating it with the addition of diethyl ether. After this process, pure MAI was obtained.

The films were deposited onto the indium tin oxide (ITO) substrates that were cleaned with soap (2%, Hellmanex) and rinsed with deionized water. Then, the substrates are rinsed with ethanol, acetone and isopropyl alcohol for 15 min by ultrasonication. After that, the substrates were dried with argon blow.

The MA_{1-x}GA_xPbI₃ films were prepared by mixing stoichiometric ratio of GAI, MAI and PbI₂ (99.9%, Sigma Aldrich). The precursors were dissolved at 45% wt in dimethylformamide (DMF) under inert atmosphere in an argon globe box. The solutions were kept under magnetic stirring at 60°C for 30 minutes. The films were deposited, inside the globe box, using the spin coating process at 5000 rpm for 20 s, then dried and annealed at 100°C for 1 h, for the MAPbI₃ samples and at 135°C for the MA_{1-x}GA_xPbI₃ samples for 15 minutes. These samples were kept in the globe box before analysis.

2.2 Thin film characterization

X-Ray Diffraction:

X-Ray diffraction patterns of perovskite films were obtained by a RIGAKU Ultima IV diffractometer in the Bragg-Bentano configuration using Cu K_α radiation ($\lambda = 1.54060$ Å).

Absorption Spectroscopy:

Absorption spectra of perovskites were calculated from the transmittance measurements obtained with an Ocean Optics HR4000 spectrometer equipped with a Si-CCD detector and an integrating sphere to collect specular and diffuse transmittance at room temperature.

Photoluminescence (PL):

Photoluminescence spectra were recorded at low temperature using an HE-closed cryostat. A 325 nm He-Cd laser was used as PL excitation source. Photoluminescence data were recorded by a Hamamatsu Si-based back-thinned CCD detector.

Field-Emission Scanning Electron Microscopy:

Surface morphology and elemental composition measurements of perovskite film samples were taken using an environmental scanning electron microscope FESEM (Quanta 200 – FEI).

3. Results and Discussion

3.1 X-Ray diffraction

[Fig. 1a](#) presents the diffractograms (XRD) of $\text{MA}_{1-x}\text{GA}_x\text{PbI}_3$ for different x values. The MAPbI_3 perovskite characteristic peaks are located at approximately 14.1° and 28.4° (2θ), corresponding to planes 100 and 200, respectively. These peaks can be observed for the MAPbI_3 and $\text{MA}_{1-x}\text{GA}_x\text{PbI}_3$ samples ($0.1 \leq x \leq 0.2$) with a GA content of up to 20%. When the GA content is above 20%, the 8.4° and 11.2° peaks, corresponding to the GA tetragonal phase become visible, indicating the solubility limit has been reached.

To determine the lattice parameter of GAPbI_3 , a Pawley refinement of the XRD spectra was carried out. A tetragonal lattice type (space group $\text{P42}_1\text{NMC}$) was found when neglecting the ITO peaks. [Fig. 1b](#) shows a good fit between the simulated and the experimental diffractograms.

In order to gain further insight into the GA incorporation, Pawley refinements of the $\text{MA}_{1-x}\text{GA}_x\text{PbI}_3$ ($x = 0, 0.1, 0.2$) XRD patterns were carried out obtaining a tetragonal lattice type (space group $\text{I4}_1\text{CM}$) and experimental and simulated data for the 100 peak are shown in [Fig. 1c](#). The addition of GA produces a slight shift toward a lower angle of the characteristic 100 and 200 MA perovskite peaks, located at 14.1° and at 28.4° , which can be attributed to the fact that GA has a larger volume than MA and the partial substitution produces an increase in the lattice parameter. [Table 1](#) summarizes the results of the Pawley refinements.

Fig. 1d shows the evolution of the lattice parameters vs GA content x . As can be seen, the cell parameter a varies almost linearly, following Vegard's law. However, parameter c slightly increases with a GA content of up to 10%. The abrupt decrease for higher concentrations than $x = 0.15$ indicates a probable lattice change.

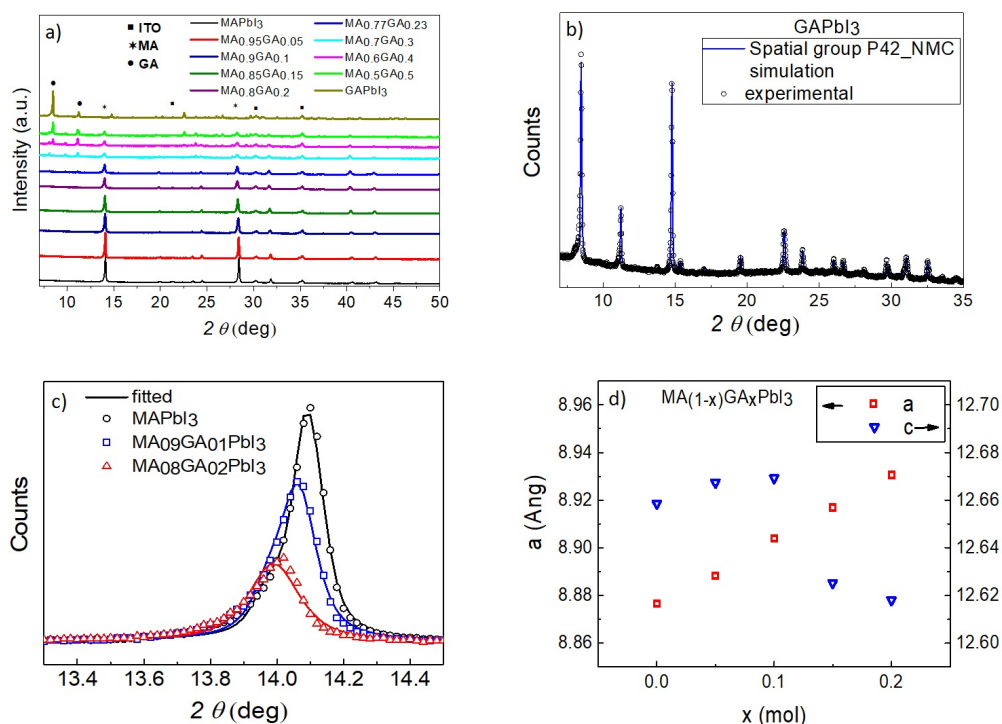


Figure 1. (a) X-ray diffractograms of $MA_{1-x}GA_xPb_3$ ($0 \leq x \leq 1$), by the spin coating process. (b) XRD spectra for pure $GAPb_3$ corresponding to the space group tetragonal P42₁NMC. (c) XRD patterns of the $MAPb_3$ and $MA_{1-x}GA_xPb_3$ with $x = 0.1, 0.2$. (d) Composition dependent evolution of lattice parameters as a function of GA content.

Table 1. Refinement factors and refined cell parameters using the Pawley method.

Sample id.	$a = b$ (Å)	c (Å)	Rwp
$MAPb_3$	8,87659	12,65859	4,42%
$MA_{0.9}GA_{0.1}Pb_3$	8,90393	12,66932	4,21%
$MA_{0.8}GA_{0.2}Pb_3$	8,93066	12,61813	3,95%
$GAPb_3$	11,97202	20,86364	5,52%

In order to evaluate the stability of mixed perovskite samples, diffractograms of $MAPb_3$ and $MA_{1-x}GA_xPb_3$ thin films were recorded immediately after sample preparation. These samples were kept at room temperature and humidity for eight

months before a control diffractogram was made. Fig. 2 shows diffractograms for MAPbI_3 and $\text{MA}_{0.9}\text{GA}_{0.1}\text{PbI}_3$ before and after eight months aging, denoted (A) and (B), respectively. As can be seen, the aged pure methylammonium perovskite shows a 12.6° peak, corresponding to PbI_2 , which evidences perovskite decomposition. Nevertheless, the diffractogram of the mixed methylammonium-guanidinium perovskite sample remains unaltered. Samples with a greater GA contents showed PbI_2 and/or GA peaks that evidence decomposition or guanidinium perovskite segregation, as can be seen in Fig. S1.

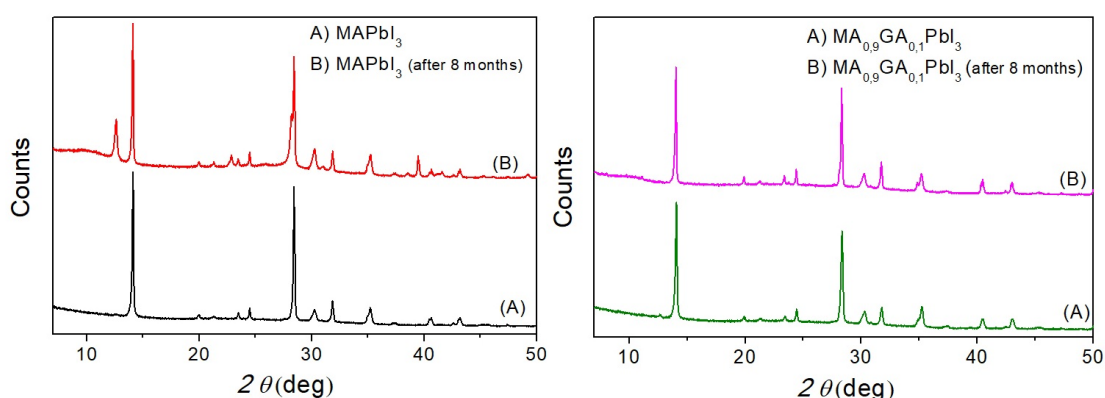


Figure 2. X-ray diffractograms of MAPbI_3 and $\text{MA}_{0.9}\text{GA}_{0.1}\text{PbI}_3$ before and after eight months.

3.2 Absorbance

Fig. 3a displays the absorption spectra for different GA values. An integrating sphere was used to collect both, specular and diffuse transmittance to reduce the effect of light scattering originated from refraction and reflection phenomena on the perovskite crystals.

The GA fraction contained in $\text{MA}_{1-x}\text{GA}_x\text{PbI}_3$ affects the optical properties. It can easily be appreciated that an increasing amount of GA results in front edge diminution, and therefore a reduction of the absorbance.

Fig. 3b provides Tauc plots showing variations in the optical bandgap. It can be observed that for the samples between 0 and 20%, the bandgap evolves very slightly towards lower energies. In Fig. 3a, a decrease of the slope for a GA contents above 20% can be appreciated, indicating a degradation of the bandgap. This result agrees with the previously suggested lattice change. Figure 3c shows a change of color varying from the black for MAPbI_3 to the yellow for GAPbI_3 .

Table 2 shows the estimated bandgap (E_g) of $MA_{1-x}GA_xPbI_3$, for samples between 0 and 20% GA contents obtained from the Fig. 3b. It can be seen that the bandgap remains almost constant, the overall variation between all the samples being 1.59 to 1.60 eV, corresponding to absorption edges spanning 775–780 nm. The inset of Fig. 3b shows the estimated bandgap (E_g) for the $GAPbI_3$ sample being 2.62 eV, corresponding to an absorption edge of 470 nm.

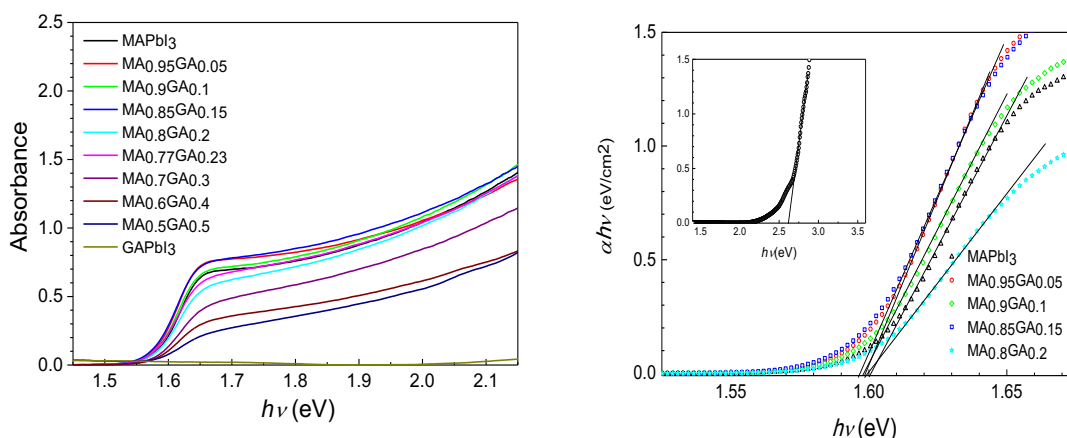


Figure 3. (a) UV-Vis absorption spectra of $MA_{1-x}GA_xPbI_3$ for different GA contents. (b) Tauc plots showing variations in optical bandgap.

Table 2. Band gap variation depending on GA content.

Sample Composition	Absorption edge at Room T	
	(eV)	(nm)
MAPbI ₃	1.60	775
MA _{0.95} GA _{0.05} PbI ₃	1.59	780
MA _{0.9} GA _{0.1} PbI ₃	1.59	780
MA _{0.85} GA _{0.15} PbI ₃	1.59	780
MA _{0.8} GA _{0.2} PbI ₃	1.59	780
GAPbI ₃	2.62	470

3.3 Photoluminescence

The photoluminescence study at different temperatures illustrates charge carrier dynamics as well as the quality of the material emission. Fig. 4a shows the PL results of $MA_{1-x}GA_xPbI_3$ ($x = 0, 0.15, 0.5, 1$) at 11 K. Intensities have been normalized to clarify the shift of the emission peaks. It can easily be observed that the position of the peak

about 800 nm for the MA-GA-based samples shifts slightly to higher wavelengths as the GA concentration increases. This behavior could be explained by the bandgap defects introduced by the GA doping. Further research is required to clarify this behavior. Moreover a pure GAPbI₃ perovskite shows a single peak located at 565 nm.

For a GA content of 50%, both peaks, at 570 and 810 nm can be observed, which is indicative of the two phases being present, as be shown in Fig. S2. In agreement with previous results for a GA content above 20%.

PL intensity of the MAPbI₃ and MA_{0.85}GA_{0.15}PbI₃ samples at 11 K is shown in Fig. 4b. MA_{0.85}GA_{0.15}PbI₃ shows a large rise in PL intensity, more than three times, that of the pure MA samples, as has been described in ref [34]. This improvement in PL can be due to the fact that the incorporation of GA reduces the amount of non-radiative levels and then the recombination takes place through radiative paths, resulting in the aforementioned improvement of PL.

Table 3 displays that the calculated bandgap at different temperatures obtained from PL measurements (Fig S3) increased as the temperature increased, as can be inferred from the evolution of the peaks towards lower wavelengths.

In this table it is worth noting that the gap energy at 11 K for MA_{0.85}GA_{0.15}PbI₃ is inferior to the gap for MAPbI₃, nevertheless this may be because the incorporation of GA produces the aforementioned supplementary energy levels above the valence band or conduction band, and the reduction of the gap, as a consequence.

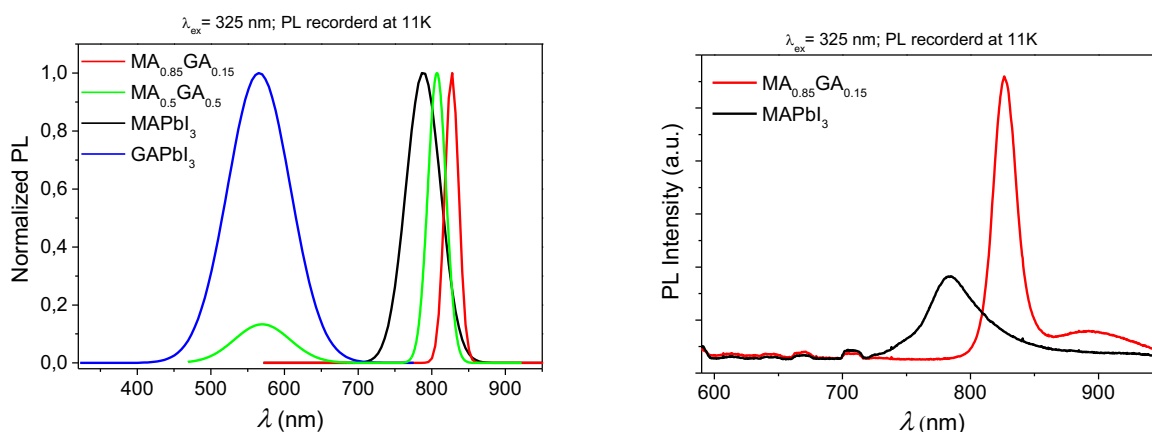


Figure 4. (a) Normalized photoluminescence emissions of MA_{1-x}GA_xPbI₃ for x = 0, 0.15, 0.5, 1 at 11 K. (b) Photoluminescence emissions of MAPbI₃ and MA_{0.85}GA_{0.15}PbI₃ recorded at 11 K.

Table 3. Band gap variation according to temperature and GA content.

Sample Composition	PL peak position at 11 K		PL peak position at 20 K		PL peak position at 70 K		PL peak position at 100 K	
	(eV)	(nm)	(eV)	(nm)	(eV)	(nm)	(eV)	(nm)
MAPbI ₃	1.57	787	1.58	785	1.58	782	1.58	782
MA _{0.85} GA _{0.15} PbI ₃	1.49	827	1.51	818	1.52	814	1.53	809
MA _{0.5} GA _{0.5} PbI ₃	1.53	807	1.53	807	1.56	795	1.56	795
GAPbI ₃	2.19	565	2.21	560	2.22	558	-	-

3.4 FESEM Analysis

SEM analysis was conducted in order to examine the impact of GA incorporation on the morphology. Fig. 5 presents top view SEM images of the MA_{1-x}GA_xPbI₃ perovskite thin films deposited on ITO substrates for x = 0, 0.15, 0.5, 1. As the amount of GA increases, the layer becomes more homogeneous, although the absorption edges shift to higher energies and then the overall absorption decreases. These results are in agreement with previous results [34].

MA_{0.85}GA_{0.15}PbI₃ needle-shape layers can be appreciated, with having a better-covered and smoother surface. The size of the needle-shape diminishes, increasing the homogeneity.

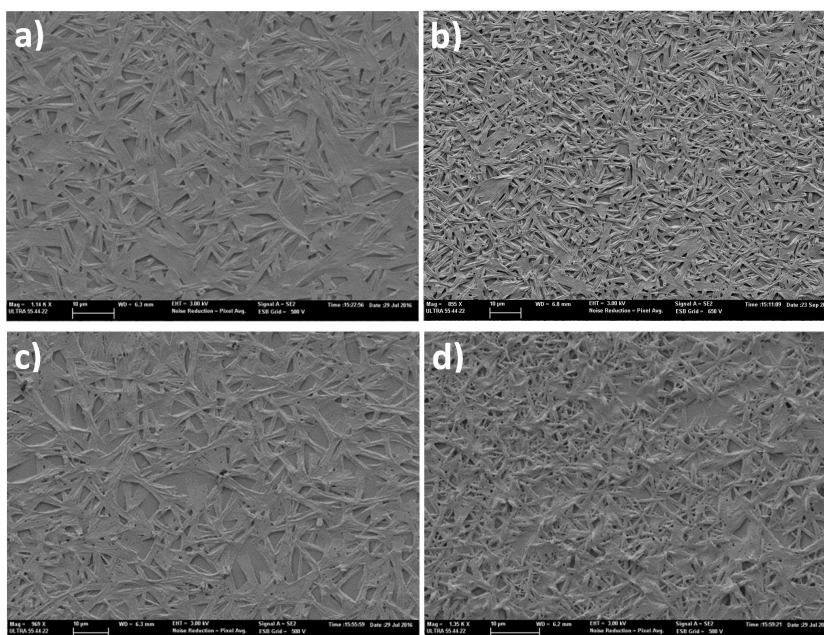


Figure 5. FESEM micrographs of perovskite thin films of (a) MAPbI₃, (b) MA_{0.85}GA_{0.15}PbI₃, (c) MA_{0.5}GA_{0.5}PbI₃ and (d) GAPbI₃.

4. Conclusions

This work reports the synthesis of $MA_{1-x}GA_xPb_3$ for different x values under an inert atmosphere, deposited on ITO substrate by spin coating. X-Ray diffraction analysis showed that the $MAPb_3$ perovskite characteristic peaks were only found in the $MA_{1-x}GA_xPb_3$ samples ($0.1 \leq x \leq 0.2$), indicating the GA incorporation in $MAPb_3$ lattice.

Tetragonal lattice type, space groups $P4_2NMC$ and $I4_{1}CM$, were found for $GAPb_3$ and $MAPb_3$, respectively. When the GA content exceeds 20%, both $MAPb_3$ and $GAPb_3$ peaks were present, indicating the solubility limit is reached.

Absorption spectra show that an increase in the GA content affects the optical properties, reducing the absorptance and therefore the light harvesting capability. Samples with a GA content between 0 and 20% showed a very slight shift towards lower energies, and samples with a GA content above 20% exhibited a decrease of the slope and, therefore, a degradation of the bandgap. The estimated bandgap (E_g) for the samples with a GA content between 0 and 20% decreased from 1.60 to 1.59 eV, corresponding to absorption edges spanning 775–780 nm.

PL results of $MA_{1-x}GA_xPb_3$ for different values of x at different temperatures showed that the position of the peaks of the GA-based samples shifts slightly to higher wavelengths as the GA concentration increases. Energy peak decreases can be explained by the bandgap defects introduced by the substitution of MA by GA. Above a GA content of 20%, peaks at 570 and 810 nm can be observed, which confirms that both phases are present.

SEM analysis images of the $MA_{1-x}GA_xPb_3$ perovskite thin films deposited on ITO substrate showed that grain continuity seems to have improved.

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